

HEF4050B-Q100

Hex non-inverting buffers

Rev. 1 — 11 November 2013

Product data sheet

1. General description

The HEF4050B-Q100 provides six non-inverting buffers with high current output capability suitable for driving TTL or high capacitive loads. Voltages in excess of the buffer supply voltage are permitted. This feature allows the buffers to be used to convert logic levels of up to 15 V to standard TTL levels. Their guaranteed fan-out into common bipolar logic elements is shown in [Table 3](#).

It operates over a recommended V_{DD} power supply range of 3 V to 15 V referenced to V_{SS} (usually ground). Unused inputs must be connected to V_{DD} , V_{SS} , or another input.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 3) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 3)
 - ◆ Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$
- Accepts input voltages in excess of the supply voltage
- Fully static operation
- 5 V, 10 V, and 15 V parametric ratings
- Standardized symmetrical output characteristics
- ESD protection:
 - ◆ MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V ($C = 200\text{ pF}$, $R = 0\text{ }\Omega$)
- Complies with JEDEC standard JESD 13-B

3. Applications

- LOCMOS (Local Oxidation CMOS) to DTL/TTL converter
- HIGH sink current for driving two TTL loads
- HIGH-to-LOW level logic conversion



4. Ordering information

Table 1. Ordering information
All types operate from -40 °C to +85 °C.

Type number	Package		
	Name	Description	Version
HEF4050BT-Q100	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1

5. Functional diagram

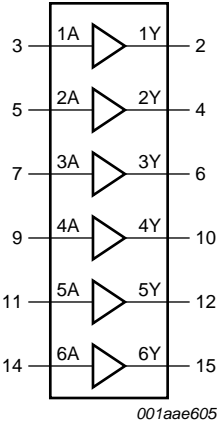


Fig 1. Logic symbol

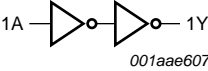


Fig 2. Logic diagram for one gate

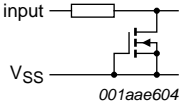


Fig 3. Input protection circuit

6. Pinning information

6.1 Pinning

HEF4050B-Q100

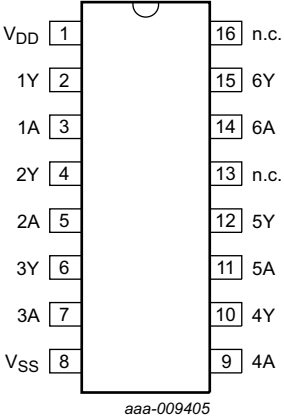


Fig 4. Pin configuration

6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
V_{DD}	1	supply voltage
1Y to 6Y	2, 4, 6, 10, 12, 15	output
1A to 6A	3, 5, 7, 9, 11, 14,	input
V_{SS}	8	ground supply voltage
n.c.	13, 16	not connected

7. Functional description

Table 3. Guaranteed fan-out

Driven element	Guaranteed fan-out
Standard TTL	2
74 LS	9
74 L	16

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DD}	supply voltage		-0.5	+18	V
I_{IK}	input clamping current	$V_I < -0.5 \text{ V}$ or $V_I > V_{DD} + 0.5 \text{ V}$	-	± 10	mA
V_I	input voltage		-0.5	$V_{DD} + 0.5$	V
I_{OK}	output clamping current	$V_O < -0.5 \text{ V}$ or $V_O > V_{DD} + 0.5 \text{ V}$	-	± 10	mA
$I_{I/O}$	input/output current		-	10	mA
I_{DD}	supply current		-	50	mA
T_{stg}	storage temperature		-65	+150	°C
T_{amb}	ambient temperature		-40	+85	°C
P_{tot}	total power dissipation	$T_{amb} -40 \text{ °C}$ to $+85 \text{ °C}$	[1] -	500	mW
P	power dissipation	per output	-	100	mW

[1] For SO16 package: P_{tot} derates linearly with 8 mW/K above 70 °C.

9. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DD}	supply voltage		3	15	V
V_I	input voltage		0	V_{DD}	V
T_{amb}	ambient temperature	in free air	-40	+85	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{DD} = 5\text{ V}$	-	3.75	$\mu\text{s/V}$
		$V_{DD} = 10\text{ V}$	-	0.5	$\mu\text{s/V}$
		$V_{DD} = 15\text{ V}$	-	0.08	$\mu\text{s/V}$

10. Static characteristics

Table 6. Static characteristics

$V_{SS} = 0\text{ V}$; $V_I = V_{SS}$ or V_{DD} unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	$T_{amb} = -40\text{ °C}$		$T_{amb} = 25\text{ °C}$		$T_{amb} = 85\text{ °C}$		Unit
				Min	Max	Min	Max	Min	Max	
V_{IH}	HIGH-level input voltage	$ I_O < 1\text{ }\mu\text{A}$	5 V	3.5	-	3.5	-	3.5	-	V
			10 V	7.0	-	7.0	-	7.0	-	V
			15 V	11.0	-	11.0	-	11.0	-	V
V_{IL}	LOW-level input voltage	$ I_O < 1\text{ }\mu\text{A}$	5 V	-	1.5	-	1.5	-	1.5	V
			10 V	-	3.0	-	3.0	-	3.0	V
			15 V	-	4.0	-	4.0	-	4.0	V
V_{OH}	HIGH-level output voltage	$ I_O < 1\text{ }\mu\text{A}$	5 V	4.95	-	4.95	-	4.95	-	V
			10 V	9.95	-	9.95	-	9.95	-	V
			15 V	14.95	-	14.95	-	14.95	-	V
V_{OL}	LOW-level output voltage	$ I_O < 1\text{ }\mu\text{A}$	5 V	-	0.05	-	0.05	-	0.05	V
			10 V	-	0.05	-	0.05	-	0.05	V
			15 V	-	0.05	-	0.05	-	0.05	V
I_{OH}	HIGH-level output current	$V_O = 2.5\text{ V}$	5 V	-	-1.7	-	-1.4	-	-1.1	mA
		$V_O = 4.6\text{ V}$	5 V	-	-0.52	-	-0.44	-	-0.36	mA
		$V_O = 9.5\text{ V}$	10 V	-	-1.3	-	-1.1	-	-0.9	mA
		$V_O = 13.5\text{ V}$	15 V	-	-3.6	-	-3.0	-	-2.4	mA
I_{OL}	LOW-level output current	$V_O = 0.4\text{ V}$	4.75 V	3.5	-	2.9	-	2.3	-	mA
		$V_O = 0.5\text{ V}$	10 V	12.0	-	10.0	-	8.0	-	mA
		$V_O = 1.5\text{ V}$	15 V	24.0	-	20.0	-	16.0	-	mA
I_I	input leakage current		15 V	-	± 0.3	-	± 0.3	-	± 1.0	μA
I_{DD}	supply current	$I_O = 0\text{ A}$	5 V	-	4.0	-	4.0	-	30	μA
			10 V	-	8.0	-	8.0	-	60	μA
			15 V	-	16.0	-	16.0	-	120	μA
C_I	input capacitance			-	-	-	7.5	-	-	pF

11. Dynamic characteristics

Table 7. Dynamic characteristics

$V_{SS} = 0\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; unless otherwise specified. for test circuit, see [Figure 6](#).

Symbol	Parameter	Conditions	V_{DD}	Extrapolation formula	Min	Typ	Max	Unit
t_{PHL}	HIGH to LOW propagation delay	nA to nY; see Figure 5	5 V	[1] $26\text{ ns} + (0.18\text{ ns/pF})C_L$	-	35	70	ns
			10 V	$16\text{ ns} + (0.08\text{ ns/pF})C_L$	-	20	35	ns
			15 V	$12\text{ ns} + (0.05\text{ ns/pF})C_L$	-	15	30	ns
t_{PLH}	LOW to HIGH propagation delay	nA to nY; see Figure 5	5 V	[1] $28\text{ ns} + (0.55\text{ ns/pF})C_L$	-	55	110	ns
			10 V	$14\text{ ns} + (0.23\text{ ns/pF})C_L$	-	25	55	ns
			15 V	$12\text{ ns} + (0.16\text{ ns/pF})C_L$	-	20	40	ns
t_{THL}	HIGH to LOW output transition time	see Figure 5	5 V	[1] $7\text{ ns} + (0.35\text{ ns/pF})C_L$	-	25	50	ns
			10 V	$3\text{ ns} + (0.14\text{ ns/pF})C_L$	-	10	20	ns
			15 V	$2\text{ ns} + (0.09\text{ ns/pF})C_L$	-	7	14	ns
t_{TLH}	LOW to HIGH output transition time	see Figure 5	5 V	[1] $10\text{ ns} + (1.00\text{ ns/pF})C_L$	-	60	120	ns
			10 V	$9\text{ ns} + (0.42\text{ ns/pF})C_L$	-	30	60	ns
			15 V	$6\text{ ns} + (0.28\text{ ns/pF})C_L$	-	20	40	ns

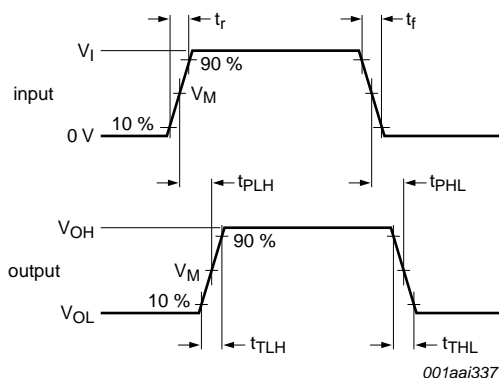
[1] The typical values of the propagation delay and transition times are calculated from the extrapolation formulas shown (C_L in pF).

Table 8. Dynamic power dissipation P_D

P_D can be calculated from the formulas shown. $V_{SS} = 0\text{ V}$; $t_r = t_f \leq 20\text{ ns}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Symbol	Parameter	V_{DD}	Typical formula for P_D (μW)	where:
P_D	dynamic power dissipation	5 V	$P_D = 3800 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$	f_i = input frequency in MHz,
		10 V	$P_D = 11600 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$	f_o = output frequency in MHz,
		15 V	$P_D = 65900 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$	C_L = output load capacitance in pF, V_{DD} = supply voltage in V, $\Sigma(f_o \times C_L)$ = sum of the outputs.

12. Waveforms



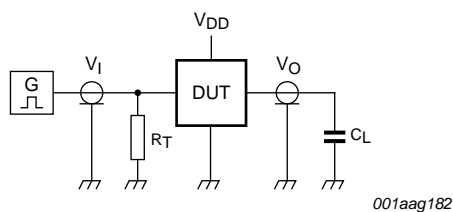
Measurement points are given in [Table 9](#).

V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 5. Input to output propagation delays

Table 9. Measurement points

Input		Output
V_M	V_I	V_M
$0.5V_{DD}$	0 V to V_{DD}	$0.5V_{DD}$



Test data is given in [Table 10](#).

Definitions for test circuit:

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

Fig 6. Test circuit for switching times

Table 10. Test data

Supply voltage	Input			Load
	V_I	V_M	t_r, t_f	C_L
5 V to 15 V	V_{DD}	$0.5V_I$	≤ 20 ns	50 pF

13. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1

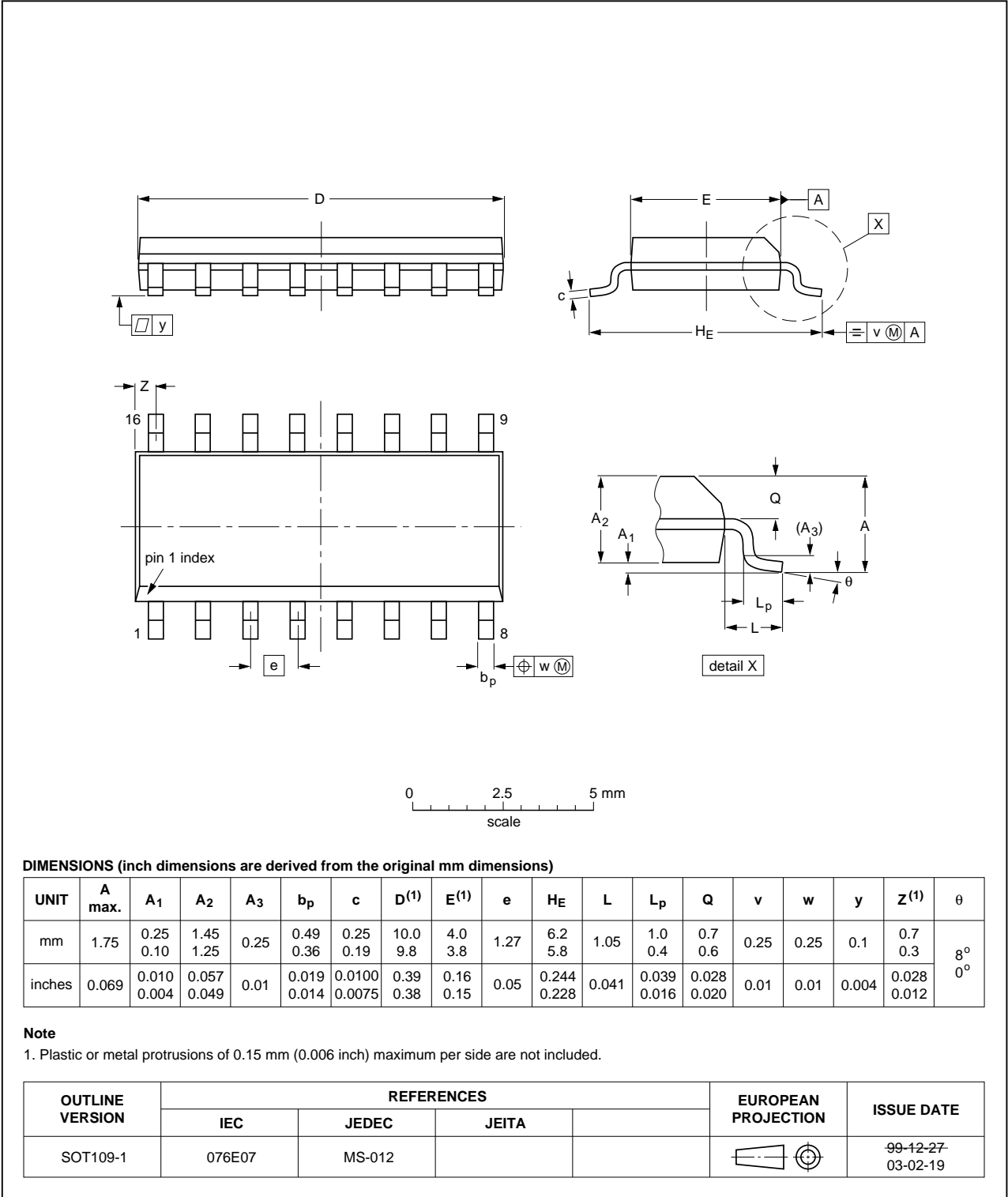


Fig 7. Package outline SOT109-1 (SO16)

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
DTL	Diode Transistor Logic
DUT	Device Under Test
LOC MOS	Local Oxidation CMOS
HBM	Human Body Model
ESD	ElectroStatic Discharge
MM	Machine Model
MIL	Military
TTL	Transistor-Transistor Logic

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
HEF4050B_Q100 v.1	20131111	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[2] The term 'short data sheet' is explained in section "Definitions".

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